N-channel 40 V, 11.0 mΩ standard level MOSFET in LFPAK33
29 January 2019 Product data sheet

1. General description

Automotive qualified standard level N-channel MOSFET in an LFPAK33 package using Trench 9 TrenchMOS technology. This product has been designed and qualified to AEC-Q101 for use in high performance automotive applications.

2. Features and benefits

- Fully automotive qualified to AEC-Q101 at 175 °C
- Trench 9 superjunction technology:
 - · Low power losses, high power density
- · LFPAK copper clip package technology:
 - · High robustness and reliability
 - · Gull wing leads for high manufacturability and AOI
- Repetitive avalanche rated

3. Applications

- 12 V automotive systems
- · Powertrain, chassis, body and infotainment applications
- Medium/Low power motor drive
- · DC-DC systems
- · LED lighting

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	35	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	50	W
Static characte	eristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 11		6.5	9.3	11	mΩ
Dynamic chara	ecteristics		•	•	'		
Q_{GD}	gate-drain charge	I _D = 10 A; V _{DS} = 32 V; V _{GS} = 10 V; Fig. 13; Fig. 14		-	2	4	nC
Source-drain d	liode		•	•	'		
Q _r	recovered charge	$I_S = 10 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}$		-	13	-	nC



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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
S		$I_S = 10 \text{ A}; \text{ dI}_S/\text{dt} = -100 \text{ A/}\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $V_{DS} = 20 \text{ V}; \text{ T}_j = 25 ^{\circ}\text{C}; \frac{\text{Fig. } 17}{\text{C}}$	-	0.59	-	

^{[1] 35}A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline		Graphic symbol
1	S	source		7	D
2	S	source			
3	S	source			G—(F)
4	G	gate			mbb076 S
mb	D	Mounting base; connected to drain	1 2 3 4 LFPAK33 (SOT1)	 210)	

6. Ordering information

Table 3. Ordering information

Type number	mber Package					
	Name	Description	Version			
BUK7M11-40H	LFPAK33	Plastic, single ended surface mounted package (LFPAK33); 8 leads; 0.65 mm pitch	SOT1210			

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7M11-40H	71140H

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit			
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	40	V			
V_{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	20	V			
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	50	W			
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	35	А			
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	34	А			
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3		-	193	А			
T_{stg}	storage temperature			-55	175	°C			
Tj	junction temperature			-55	175	°C			
Source-drain	Source-drain diode								

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Symbol	Parameter	Conditions		Min	Max	Unit		
Is	source current	T _{mb} = 25 °C		-	35	Α		
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$		-	193	Α		
Avalanche rugg	Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 35 A; $V_{sup} \le 40$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[2] [3]	-	16	mJ		

^{[1] 35}A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Refer to application note AN10273 for further information.

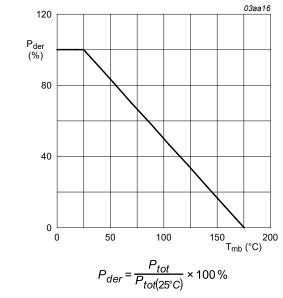
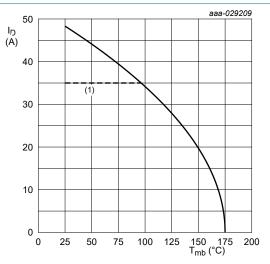


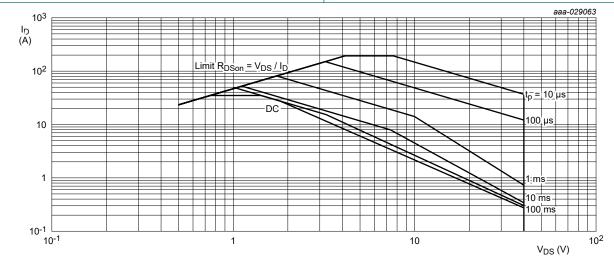
Fig. 1. Normalized total power dissipation as a function of mounting base temperature



V_{GS} ≥ 10 V

(1) 35A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

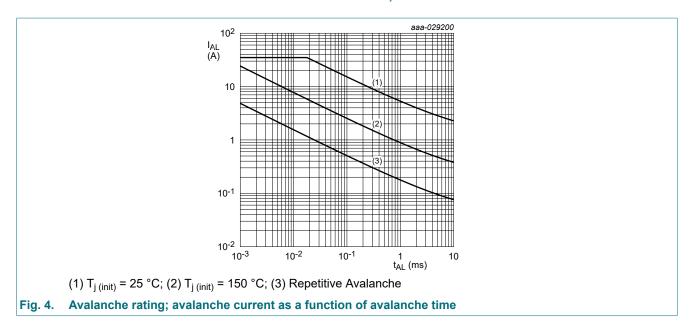
Fig. 2. Continuous drain current as a function of mounting base temperature



T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

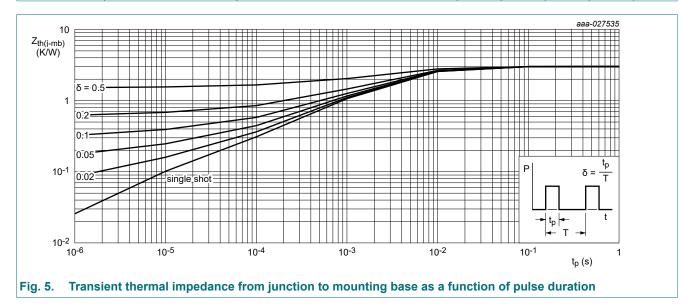
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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	2.79	3	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	cteristics		•				
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C		40	43	-	V
, ,	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -40 ^{\circ}C$		-	40.5	-	V

BUK7M11-40H

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	36	40	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	2.4	3	3.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 10$	-	-	4.3	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	1	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	0.02	1	μA
		V _{DS} = 16 V; V _{GS} = 0 V; T _j = 125 °C	-	0.32	10	μΑ
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-	23	500	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 11	6.5	9.3	11	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 105 °C; Fig. 12	8.9	13.4	16.5	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 125 °C; Fig. 12	9.8	14.5	17.7	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 175 °C; Fig. 12	11.9	17.6	21.3	mΩ
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	0.3	0.9	2.3	Ω
Dynamic ch	haracteristics		,			
Q _{G(tot)}	total gate charge	I _D = 10 A; V _{DS} = 32 V; V _{GS} = 10 V;	-	11.2	16	nC
Q _{GS}	gate-source charge	Fig. 13; Fig. 14	-	3.4	5.1	nC
Q _{GD}	gate-drain charge		-	2	4	nC
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;	-	730	1022	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	288	403	pF
C _{rss}	reverse transfer capacitance		-	35	77	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 3 \Omega; V_{GS} = 10 \text{ V};$	-	4.3	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	2.3	-	ns
t _{d(off)}	turn-off delay time	1	-	8.3	-	ns
t _f	fall time		-	3.6	-	ns
Source-dra	in diode					
V_{SD}	source-drain voltage	I _S = 10 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 16</u>	-	0.84	1.2	V
t _{rr}	reverse recovery time	$I_S = 10 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}; Fig. 17$	-	20	-	ns
Q _r	recovered charge	I_S = 10 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V	-	13	-	nC
S	softness factor	$I_S = 10 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 17$	-	0.59	-	
		I_S = 10 A; dI_S/dt = -500 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; T_i = 25 °C; Fig. 17	-	0.38	-	

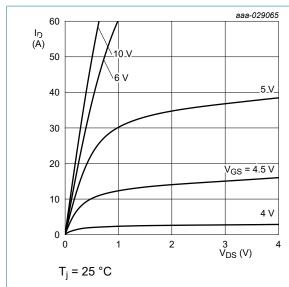


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

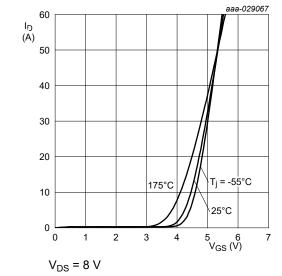


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

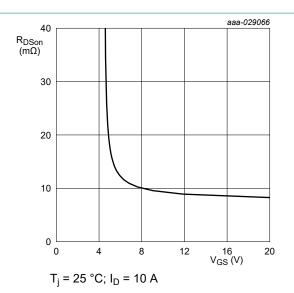


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

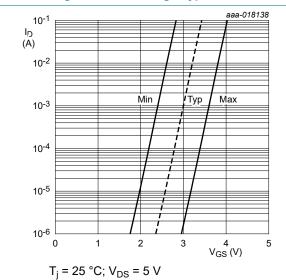


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

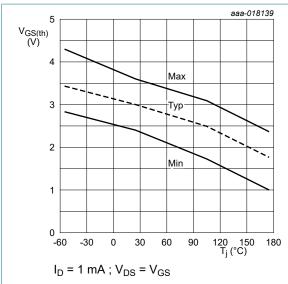


Fig. 10. Gate-source threshold voltage as a function of junction temperature

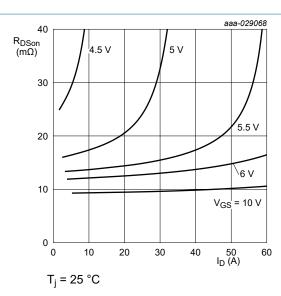


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

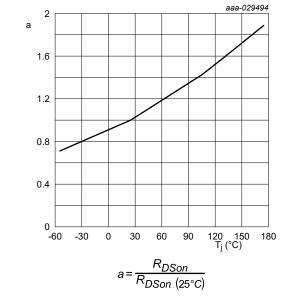


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

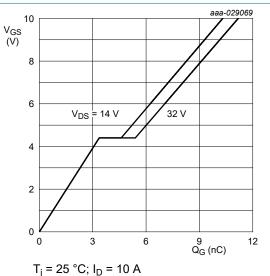


Fig. 13. Gate-source voltage as a function of gate charge; typical values

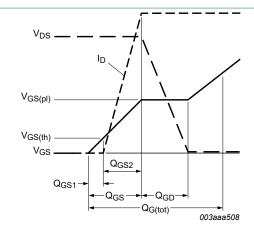
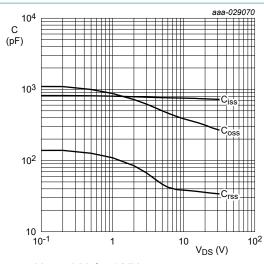


Fig. 14. Gate charge waveform definitions



 $V_{GS} = 0 V$; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

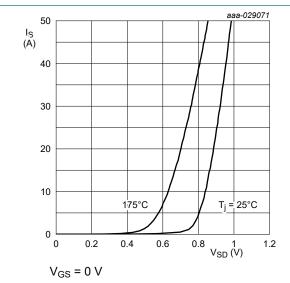


Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

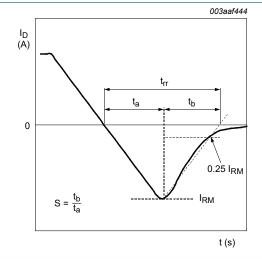


Fig. 17. Reverse recovery timing definition

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11. Package outline

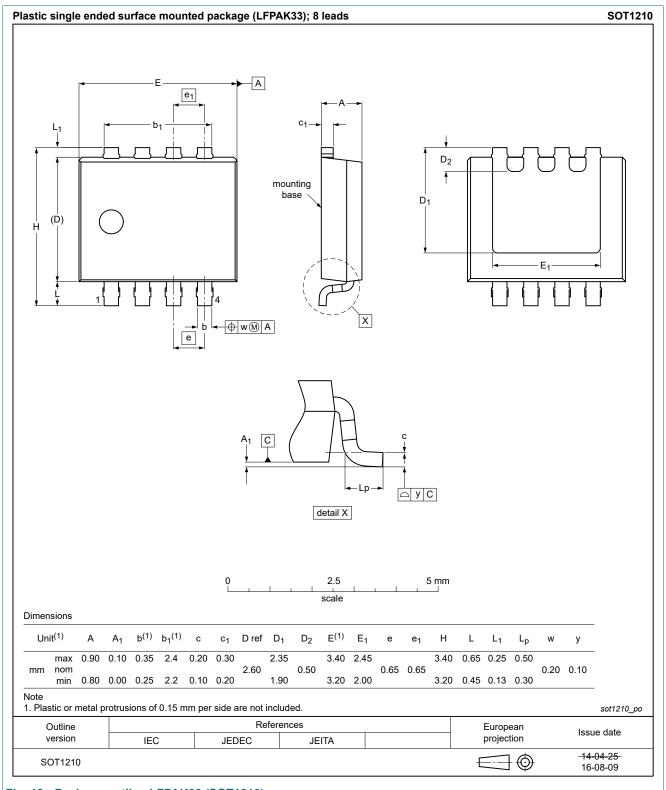


Fig. 18. Package outline LFPAK33 (SOT1210)

N-channel 40 V, 11.0 mΩ standard level MOSFET in LFPAK33

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Document status [1][2]	Product status [3]	Definition
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